NSN 5961-01-083-8873

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Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-083-8873 **Inclosure Material:** Glass **Overall Length:** Between 0.130 inches and 0.300 inches **Overall Diameter:** Between 0.115 inches and 0.165 inches **Mounting Method: Terminal Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 150.0 working peak reverse voltage **Current Rating Per Characteristic:** 6.00 amperes forward current, total rms megahertz **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius junction **Test Data Document:** 81349-mil-s-19500/477 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 2 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: